RoHS COMPLIANT

N-Channel 650 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^a	Q _g (Typ.)		
650	1.1 at V _{GS} = 10 V	5	12.5		

FEATURES

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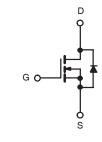
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- DT-Trench Power MOSFET •
- 100 % Rg and UIS Tested •

APPLICATIONS

- Flyback for SMPS
- Charger, Adapter, lighting





N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	650	v		
Gate-Source Voltage		V _{GS}	± 30	V	
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	I _D	5 4.6 1.1 ^{b, c} 0.8 ^{b, c}	A	
Pulsed Drain Current (t = 300 µs)	·	I _{DM}	20	A	
Continuous Source-Drain Diode Current	T _C = 25 °C T _A = 25 °C	I _S	5 1.0 ^{b, c}		
Single Pulse Avalanche Current		I _{AS}	4.8		
Single Pulse Avalanche Energy	le Pulse Avalanche Energy L = 0.1 mH		8.3	mJ	
Maximum Power Dissipation	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	P _D	110 70.4 5.1 ^{b,c} 3.26 ^{b, c}	W	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	℃		
Soldering Recommendations (Peak Temperature		260			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	25	50	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	0.9	1.2	0/ 11		

Notes:

a. Based on $T_C = 25$ °C. b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.
d. The DFN5X6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 70 °C/W.

Parameter	Symbol Test Conditions			Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$	650			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		0.65		V/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_{\rm D} = 250 \ \mu \text{A}$		- 5.8		V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2		4	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zara Cata Valtaga Drain Current		$V_{DS} = 650 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	5			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 1 A		1.1	1.5	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 1 A		2.3		S
Dynamic ^b	11				1	
Input Capacitance	C _{iss}			450		pF
Output Capacitance	C _{oss}	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		26		
Reverse Transfer Capacitance	C _{rss}			3		
Total Gate Charge	Q _q			12.5		nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 480 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A}$		4.5		
Gate-Drain Charge	Q _{gd}			3.2		
Gate Resistance	R _g	f = 1 MHz		6		Ω
Turn-On Delay Time	t _{d(on)}			20		
Rise Time	t _r	V_{DD} = 480 V, R_L = 5 Ω	-	11		- ns
Turn-Off Delay Time	t _{d(off)}	${\sf I}_{\sf D}\cong$ 1 A, ${\sf V}_{\sf GEN}$ = 10 V, ${\sf R}_{\sf g}$ = 1 Ω		45		
Fall Time	t _f			8		
Drain-Source Body Diode Characteristic	s		•		•	
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			5	
Pulse Diode Forward Current ^a	I _{SM}				20	A
Body Diode Voltage	V _{SD}	I _S = 1 A		0.7	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			205	1	ns
Body Diode Reverse Recovery Charge	Q _{rr}	L = 1.0 dt/dt = 100.0/up T = 05.00		2		μC
Reverse Recovery Fall Time	ta	l _F = 1 A, dl/dt = 100 A/μs, T _J = 25 °C		27		
Reverse Recovery Rise Time	t _b			34	1	ns

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

55 °C

5

4

80

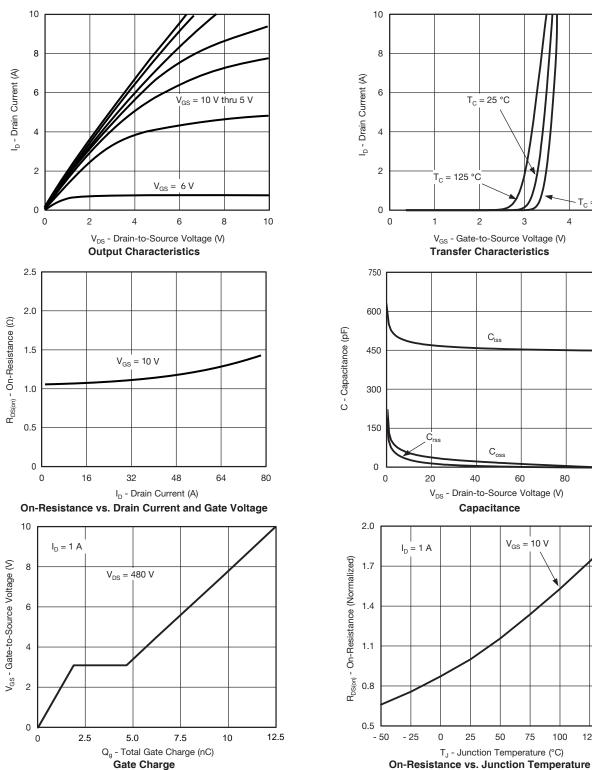
100

125

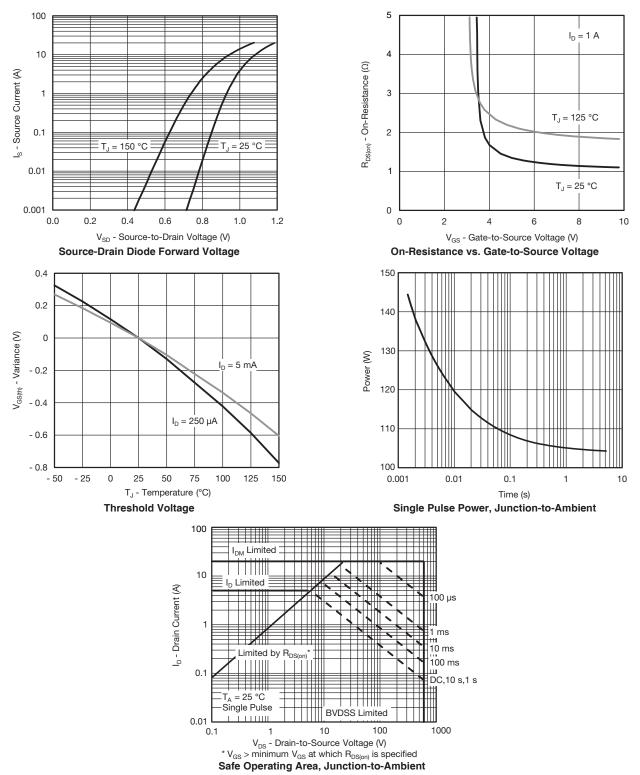
150

100

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

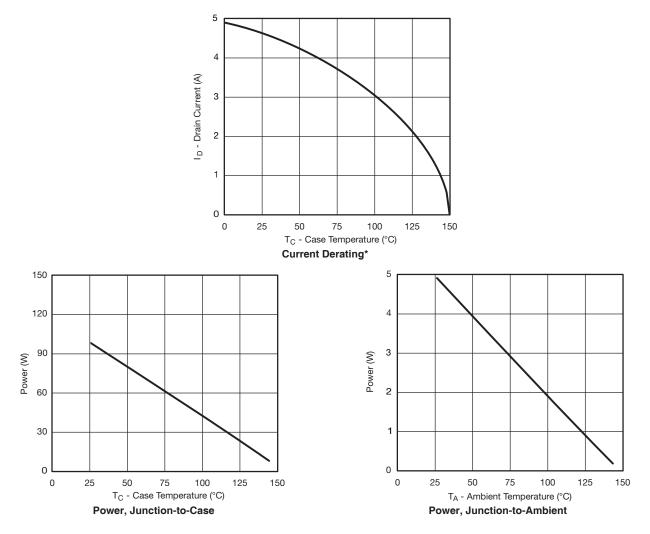


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

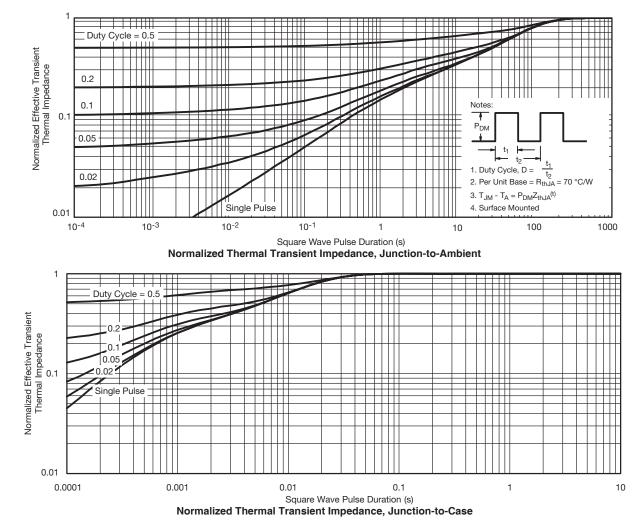


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



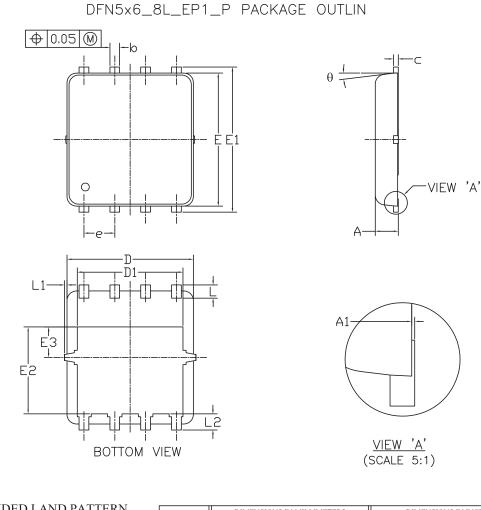
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

6





RECOMMENDED LAND PATTERN 4.60 0.50 . -0.77 -0.55 _ П -0.635 4.12 6.15 1,60 + 0.65 + ++ ł -1.27-0.50-

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
с	0.15	0.20	0.25	0.006	0.008	0.010
D	4.80	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0.15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°

UNIT: mm

NOTE 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.

MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.

2. CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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